

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT
APPLICATIONREQUEST FOR FILING APPLICATION
Under Rule 53(a), (b) & (f)
(N Filing Fee or Oath/Declaration)
(Do NOT use for Provisional or PCT Applications)
Use for Design or Utility Applications

00909

RULE 53(f) NO DECLARATIONHon. Commissioner of Patents
Washington, DC 20231

Atty. Dkt.

P 2800192

M#

EL00028CDC

Client Ref

Date:

April 17, 2001

Sir:

1. This is a Request for filing a new Patent Application(☐ Design ☒ Utility) entitled:

2. (Complete) Title:

FABRICATING PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD
PROCESS OF A METAL FILM

without a filing fee or Oath/Declaration but for which is enclosed the following:

3. ☒ Abstract 1 page(s).

4. 24 Pages of Specification (only spec. and claims);

5. ☐ Specification in non-English language

6. 14 Numbered claim(s); and

7. ☒ Drawings: 13 sheet(s) ☐ 1 set informal;8. ☒ formal of size: ☒ A4 ☐ 11"9. **DOMESTIC/INTERNATIONAL** priority is claimed under 35 USC 119(e)/120/365(c) based on the following provisional, nonprovisional and/or PCT international application(s):

Application No.	Filing Date	Application No.	Filing Date
(1)		(2)	
(3)		(4)	
(5)		(6)	

10. **FOREIGN** priority is claimed under 35 USC 119(a)-(d)/365(b) based on filing in

JAPAN

Application No.	Filing Date	Application No.	Filing Date
(1) 2000-115187	April 17, 2000	(2)	
(3)		(4)	
(5)		<input type="checkbox"/> See 3 rd page for additional priorities	

11. 1 (No.) Certified copy (copies): ☒ attached; ☐ previously filed (date) _____
in U.S. Application No. _____ / filed on _____12. ☐ This is a reissue of Patent No. _____13. ☐ See top first page re prior Provisional, National, International application(s) (X box only if info is there and do not complete item 14 or 15.)

14. This application claims benefit of the following prior US application(s), the contents of which are incorporated into this application by this reference:

No. / filed _____
 No. / filed _____
 No. / filed _____
 No. PCT / filed _____, which

Designated the U.S. and that International Application ☐ was ☐ was not published under PCT Article 21(2) in English15. ☐ See the attached Preliminary Amendment, which amends the specification to claim benefit of the above listed US applications16. Extension to date: ☐ concurrently filed ☐ not needed ☐ previously filed17. ☐ Small Entity Status is claimed (**pre-filing confirmation required**)17(a) ☐ Attached: (No.) Small Entity Statement(s). (Since 9/8/00 Small Entity Statement not essential to make claim)17(b) ☐ See **NONPUBLICATION REQUEST** under Rule 213(a) attached (Pat-258)

18. ☐ Assignee (optional): _____

19. ☐ Attached:

20. This application is made by the following named inventor(s) (Double check instructions for accuracy.):
(Listing of inventor(s) not a requirement, but list if known)

(1) Inventor	Tomohisa		HOSINO
	First	Middle Initial	Family Name
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(include Zip Code)			

(2) Inventor	Vincent		VEZIN
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(3) Inventor	Gishi		CHUNG
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(include Zip Code)			

(4) Inventor			
	First	Middle Initial	Family Name
Residence			
	City	State/Foreign Country	Country of Citizenship
Mailing Address			
(include Zip Code)			

(5) Inventor			
	First	Middle Initial	Family Name
Residence			
	City	State/Foreign Country	Country of Citizenship
Mailing Address			
(include Zip Code)			

21. NOTE: FOR ADDITIONAL INVENTORS, "X" ☐ and list additional inventors on attached sheet (incorporated by reference)

Pillsbury Winthrop LLP
Intellectual Property Group



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NOTE: File in duplicate with 2 post card receipts (PAT-103) & attachments

APPLICATION UNDER UNITED STATES PATENT LAWS

Atty. Dkt. No. PW 280192
(M#)

Invention: FABRICATING PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD
PROCESS OF A METAL FILM

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This is a:

- ☐ Provisional Application
- ☒ Regular Utility Application
- ☐ Continuing Application
 - ☐ The contents of the parent are incorporated by reference
- ☐ PCT National Phase Application
- ☐ Design Application
- ☐ Reissue Application
- ☐ Plant Application
- ☐ Substitute Specification
 - Sub. Spec Filed _____
 - in App. No. _____ / _____
- ☐ Marked up Specification re
Sub. Spec. filed _____
In App. No. _____ / _____

SPECIFICATION